

# PATENT ABSTRACTS OF JAPAN

(11) Publication number : 10-223897

(43) Date of publication of application : 21.08.1998

(51) Int.CI.

H01L 29/78  
H01L 21/28  
H01L 21/316  
H01L 21/3205  
H01L 21/768

(21) Application number : 09-033208

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(22) Date of filing : 31.01.1997

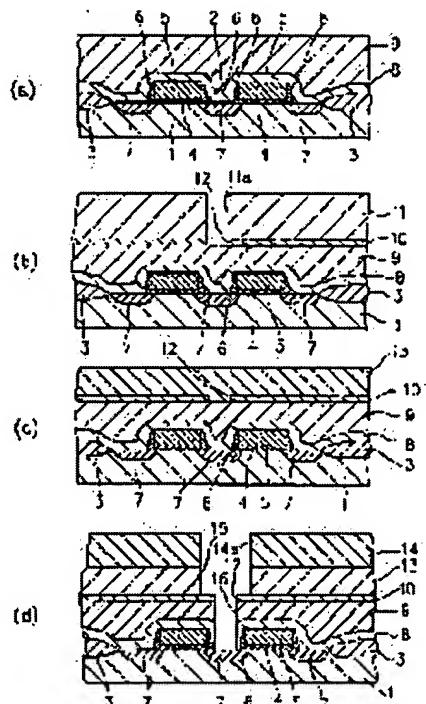
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## (54) SEMICONDUCTOR DEVICE AND ITS MANUFACTURE

### (57) Abstract:

**PROBLEM TO BE SOLVED:** To form easily and with reliability connection holes and wiring layers by photolithography using high-resolution resist.

**SOLUTION:** Interlayer insulating films 8 and 9 are formed which cover gate electrode films 5 and impurities diffusion layers 7. A silicon nitride film 10 is formed on the interlayer insulating film 9 which exhibits a lower etching speed and a smaller film thickness than the interlayer insulating films 8 and 9. A hole 12 is made in the silicon nitride film 10 with a diameter equal to a desired contact hole. An interlayer insulating film 13 is formed on the silicon nitride film 10. A wiring slot 15 wider than the diameter of the hole is formed in the interlayer insulating film 13. A contact hole 16 in analogy to the hole 12 is formed in the interlayer insulating films 8 and 9 by using the silicon nitride film 10 as a mask.



## LEGAL STATUS

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